

High-Sensitivity LEIS Principles & Applications

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- **Introduction to LEIS**

- **Miscellaneous Applications**

Imaging, NPs, segregation, surface modification, anti-wetting, NPs

- **Outer surface oxides**

- **SOFC, membranes**

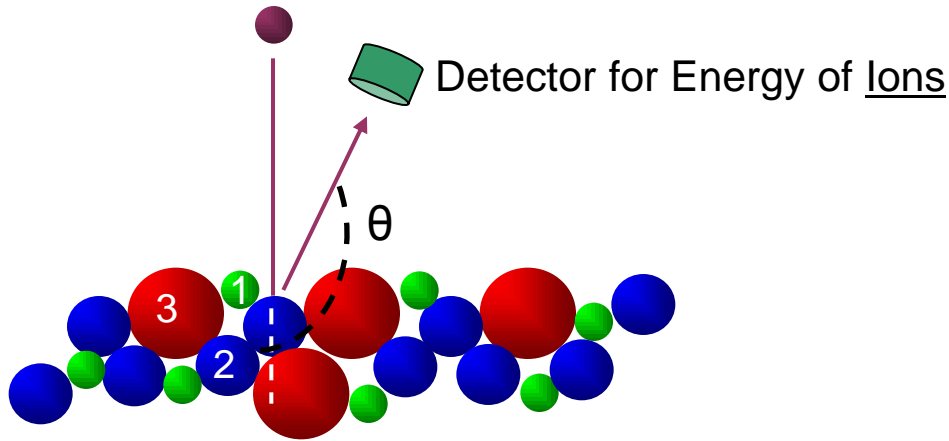
- **Growth**

- **Summary**

Low Energy Ion Scattering

Studying the outermost surface of any material

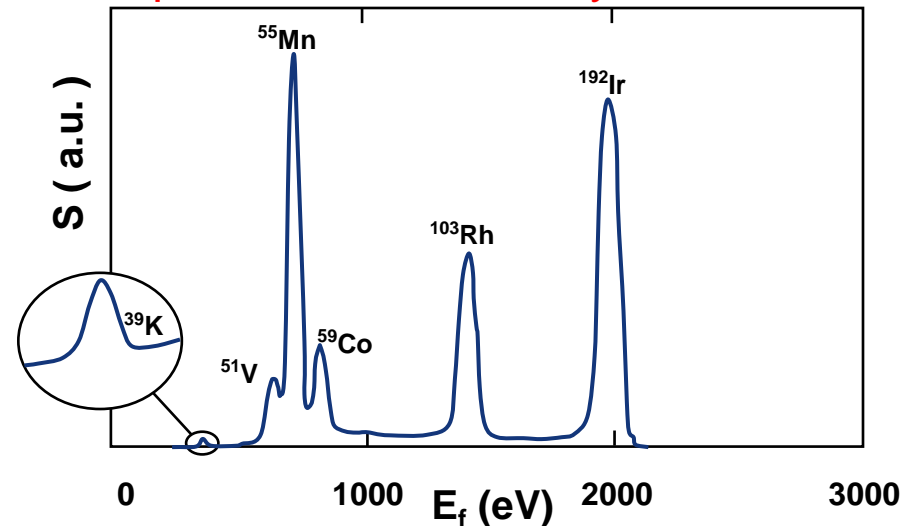
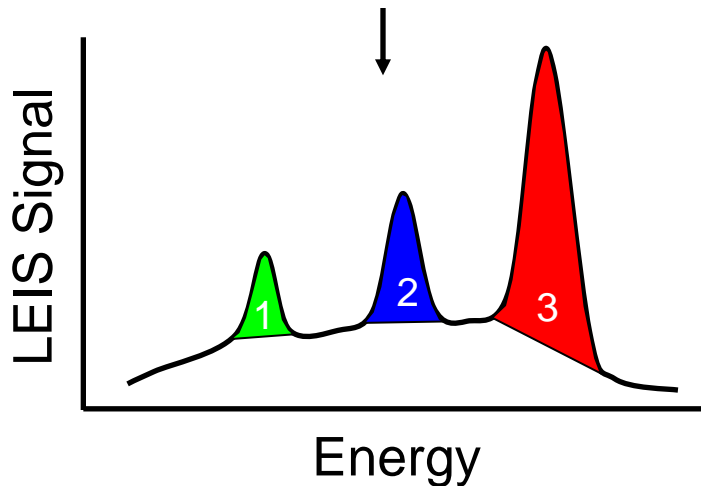
$^3\text{He}^+$, $^4\text{He}^+$, Ne^+ , Ar^+
1- 8 keV



Characteristics of the technique

- Atomic composition of outermost atomic layer
- Energy 1 – 8 keV
- Lateral resolution 0.01 – 1 mm
- In-depth (0 – 10 nm)
- No matrix effects

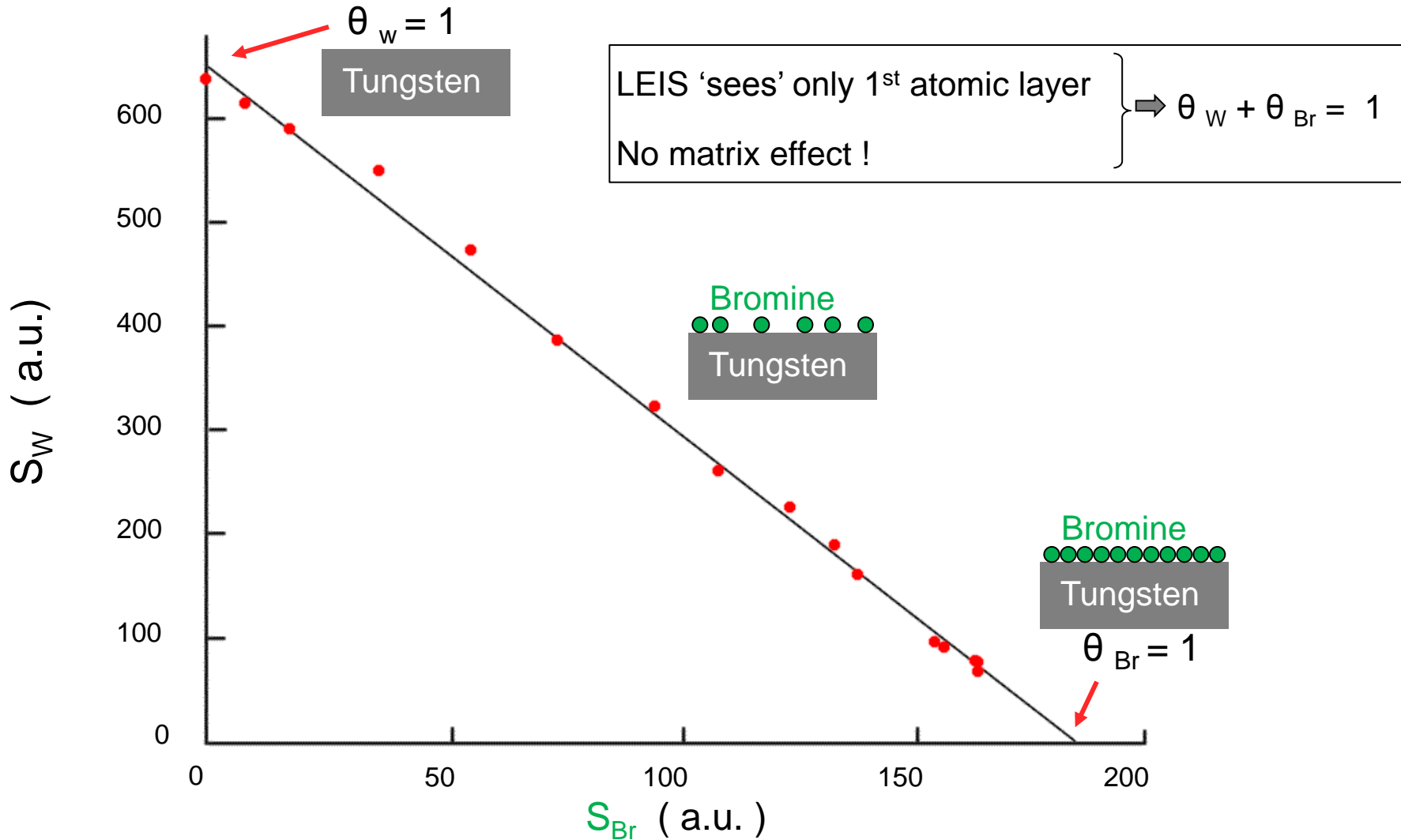
Example: 3 keV Ne → alloy



LEIS Enables Simple Quantification

Example: Coverage of Bromine adsorbed on Tungsten

LEIS can quantify the surface coverage θ in the 1st atomic layer



Qtac: Unique new Analyser

High – Sensitivity LEIS

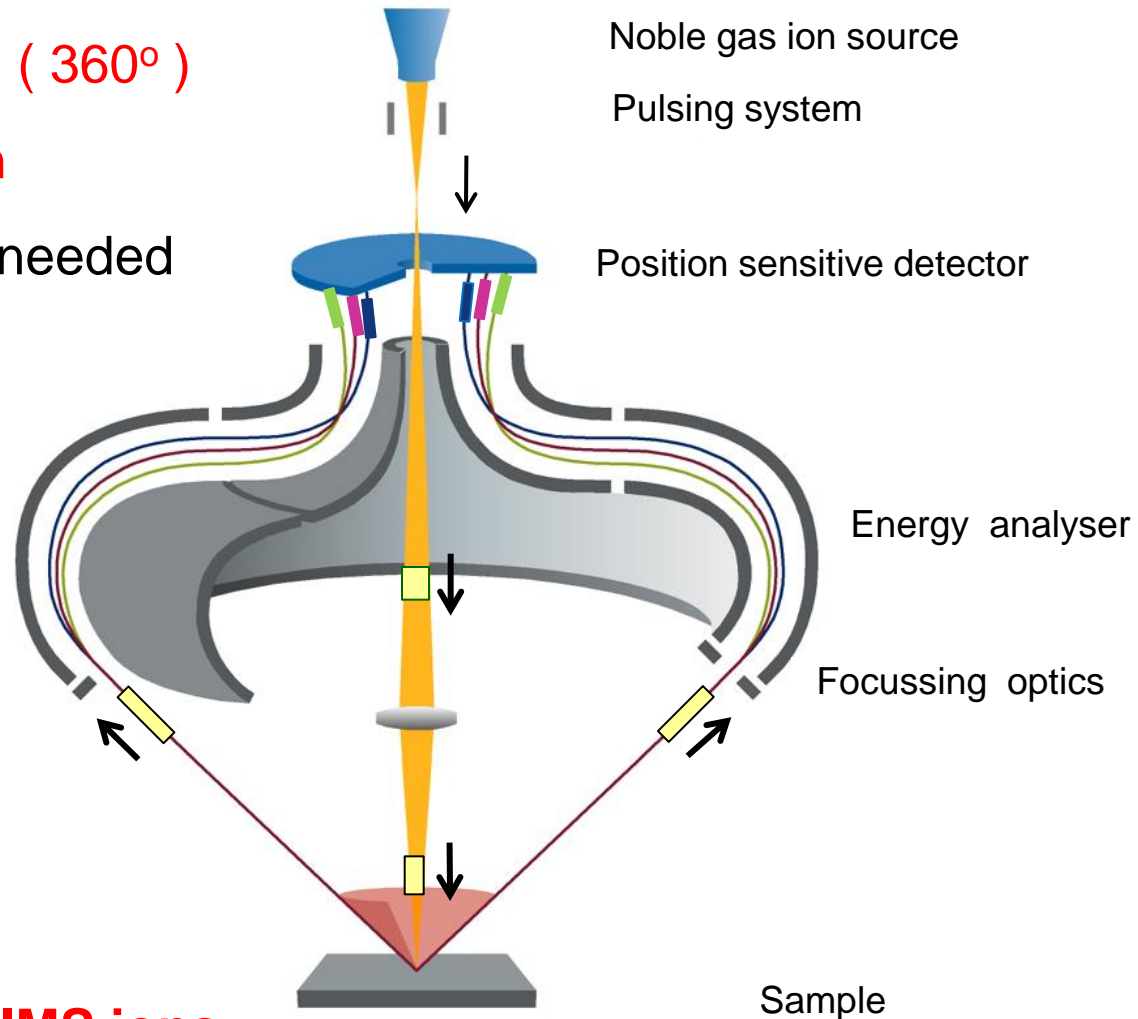
- Large acceptance angle (360°)
- Parallel energy detection
 - only low ion fluence needed



STATIC LEIS

“ Analysis *before* Damage ”
“ Hit same place only once ”
(Core/shell nanoclusters !)

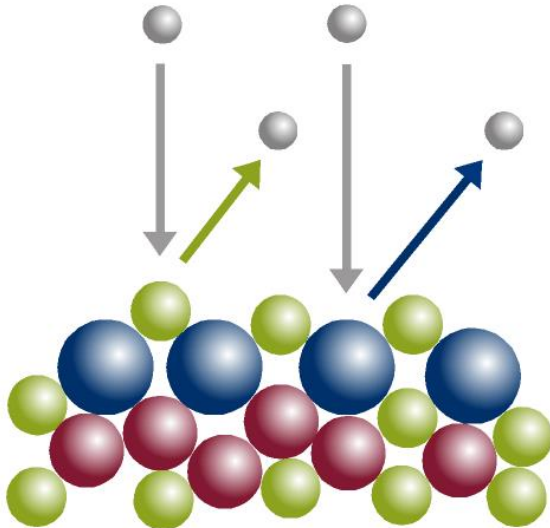
ToF filtering eliminates SIMS ions



Sample

Features of Low Energy Ion Scattering (LEIS)

He⁺, Ne⁺, Ar⁺, Kr⁺
1 - 8 keV



LEIS Features for elemental surface analysis:

- Ultra-high surface sensitivity, **top atomic layer**
- Reliable and straight-forward **quantification**
- **Non destructive** (static) analysis
- Detection limits:

Li - O $\geq 1\%$ **of 1 ML**

F - Cl 1% - 0.05% **of 1 ML**

K - U 500 ppm - 10 ppm **of 1 ML**

- **Static depth profiling** (up to 10 nm)

Reviews

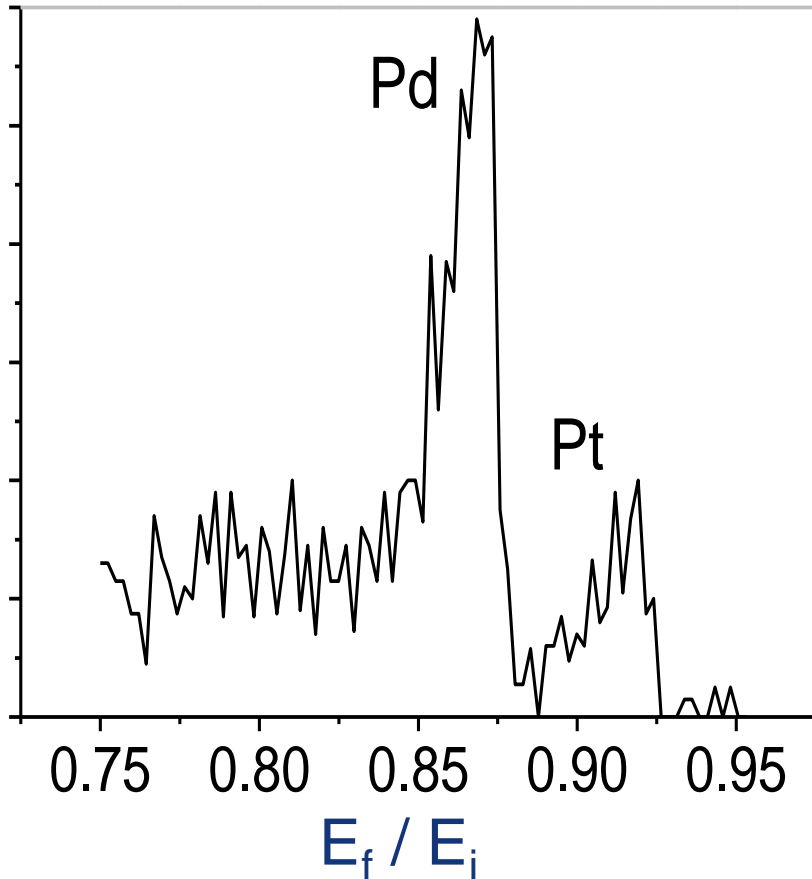
- Brongersma et al., Surf. Sci. Rep. 62 (2007) 63
- H.H. Brongersma, Low-Energy Ion Scattering in: Characterization of Materials, Ed. E.N. Kaufmann, pp. 2024-2044, Wiley (2012).

Conventional LEIS vs HS - LEIS

Pd / Pt-C (1000 m²/g)

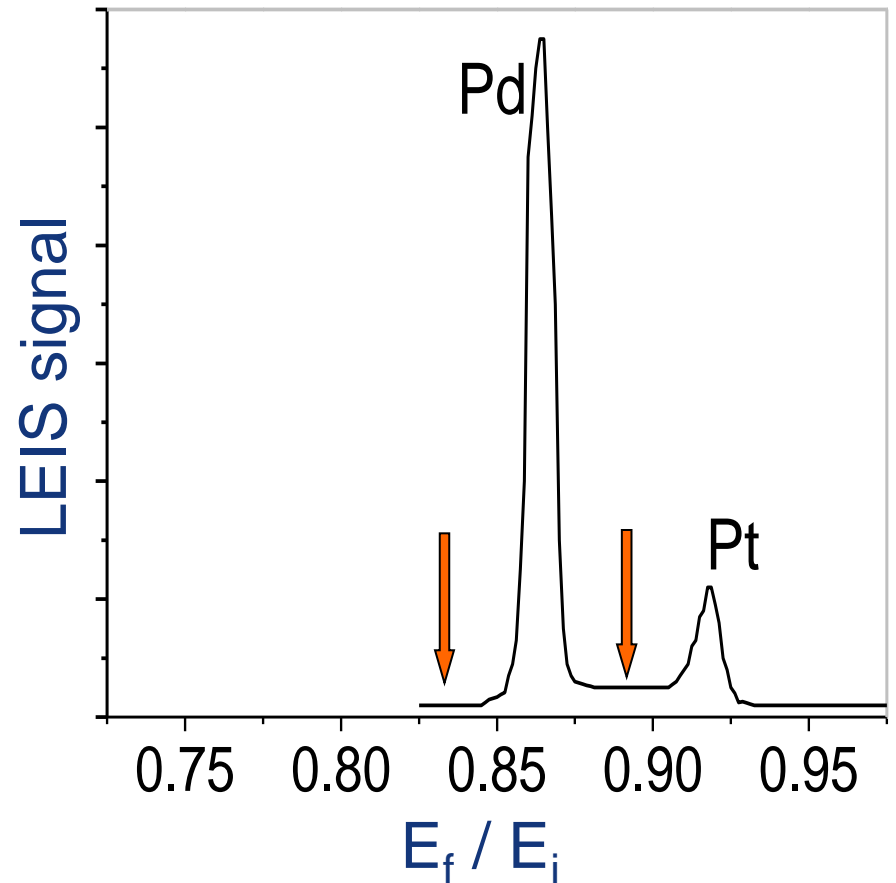
Conventional LEIS

⁴He 10,000 nC



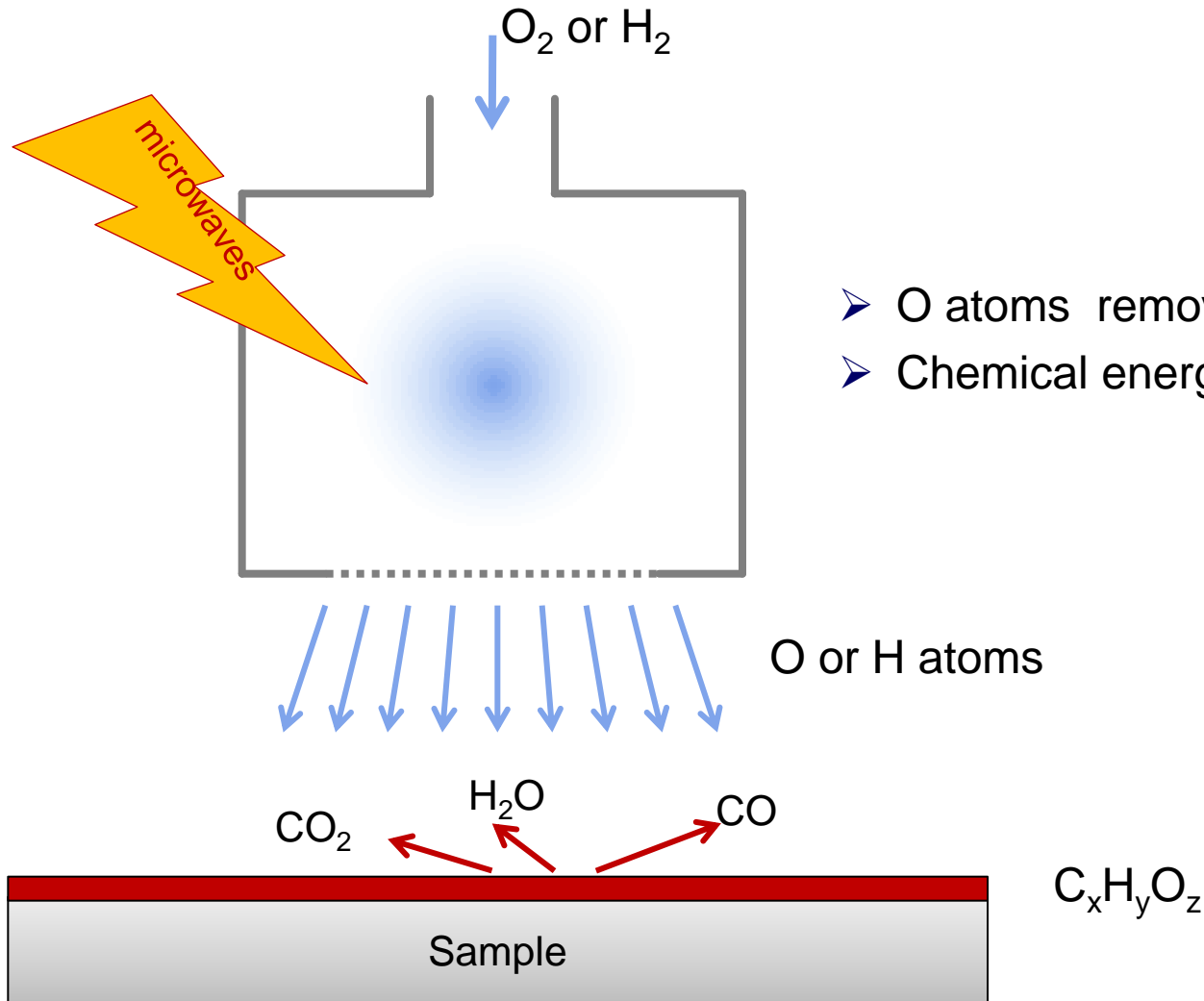
High-Sensitivity LEIS

⁴He 5.4 nC



Sample Cleaning

Atom Source for O- and H-atoms

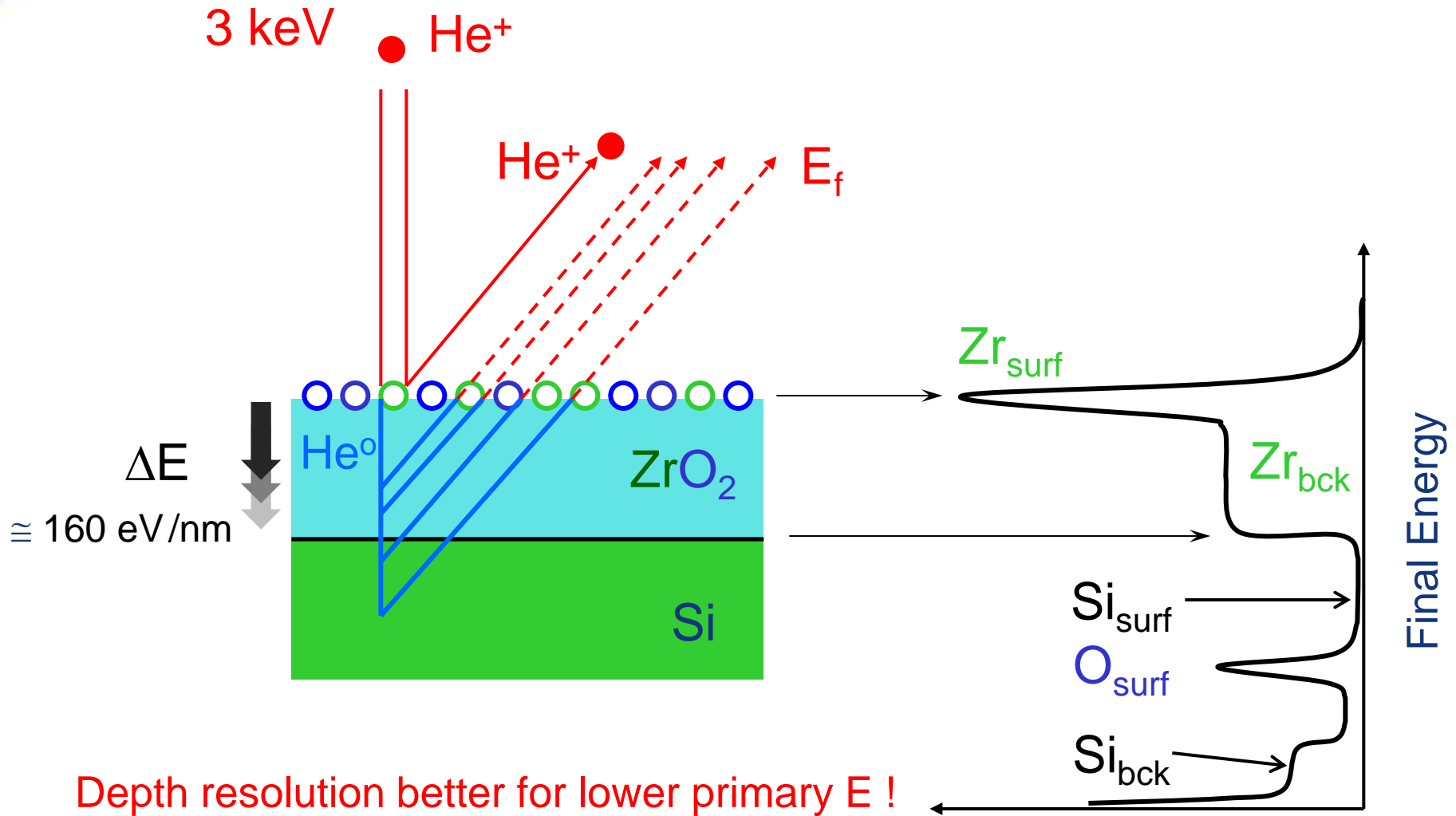


- O atoms remove organics, coke
- Chemical energy: *no sputtering*

Two possibilities:

- 1. Static LEIS + Sputter depth profiling with dual ion beam
(advantage of quantification, depth resolution LEIS)
- 2. Static LEIS (non destructive) for heavier elements
(analogous to RBS and MEIS, but better depth resolution)

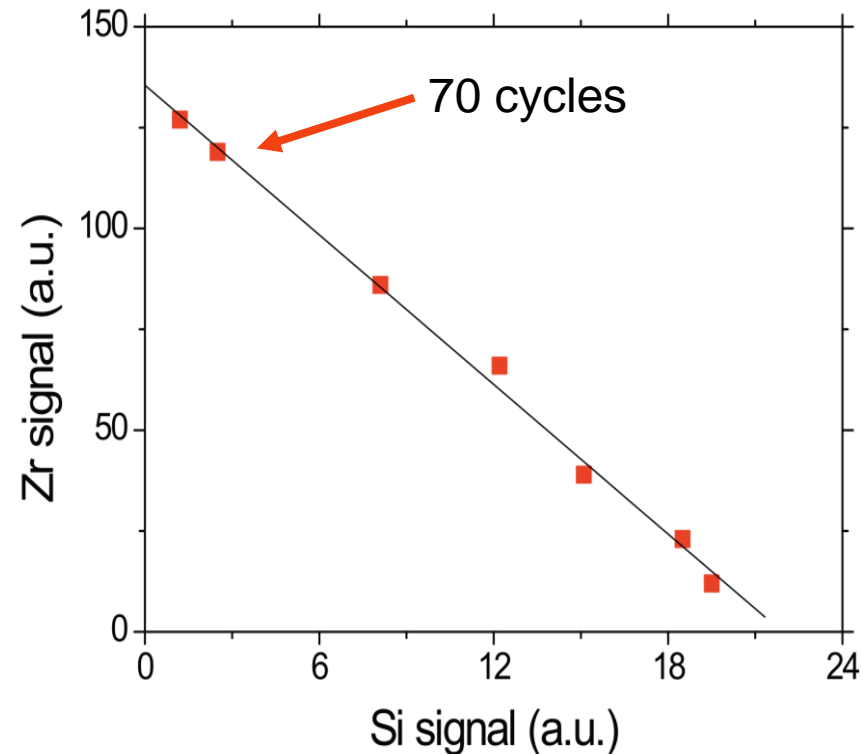
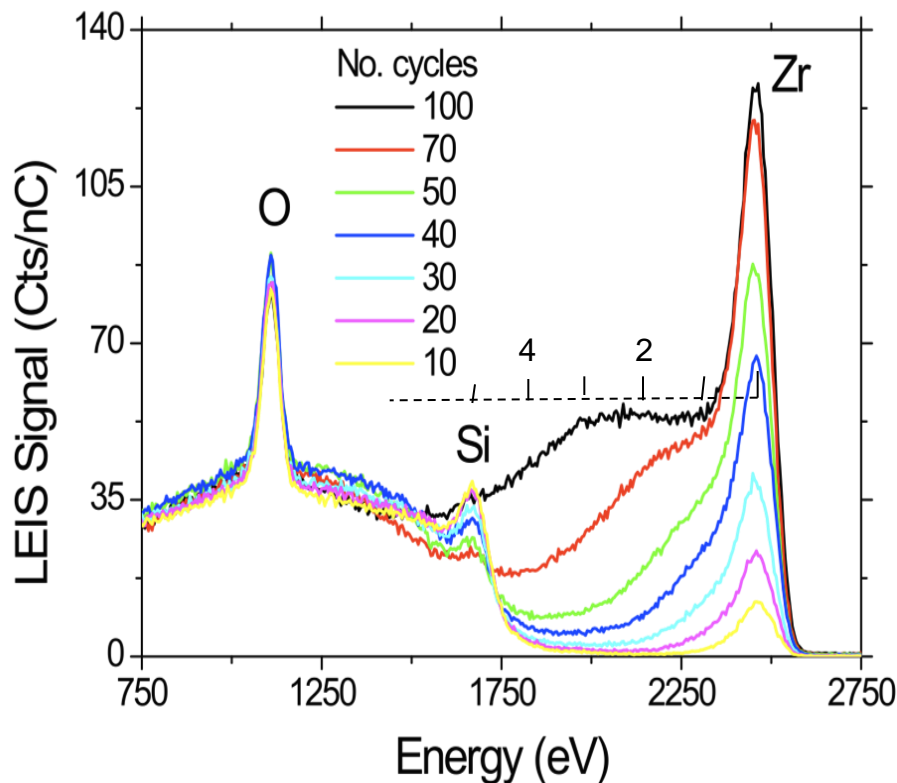
Depth info; non-destructive



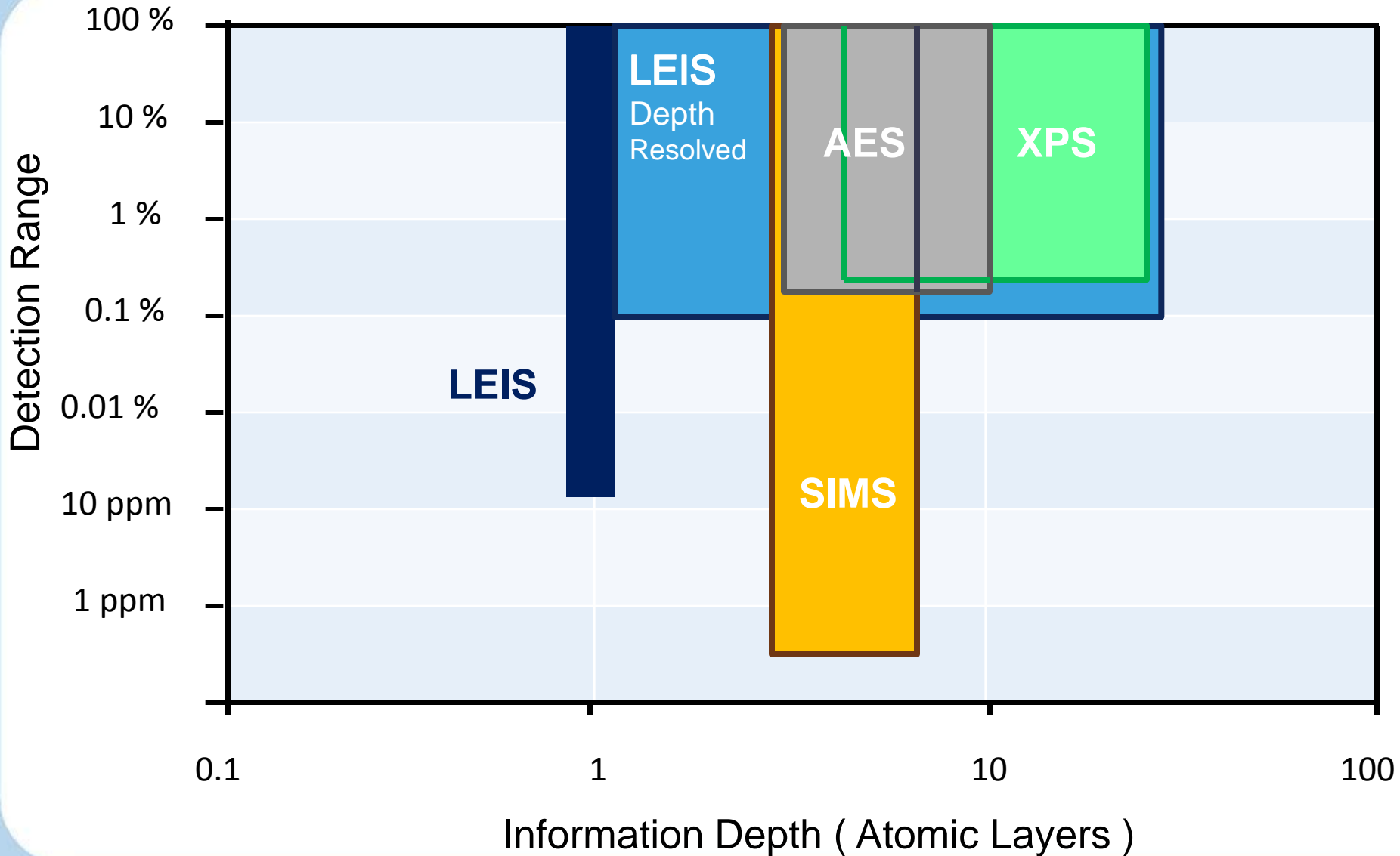
1st atom and Static Depth Profile

ZrO₂ Atomic Layer Deposition on Silicon

- Detection / quantification pinholes (still present after 70 cycles)
- Thickness distribution ZrO₂ layer (160 eV/nm)
- No matrix effect
- Example: calibration / quantification for a 2 component system



Detection range vs Information Depth for AES, LEIS, SIMS and XPS

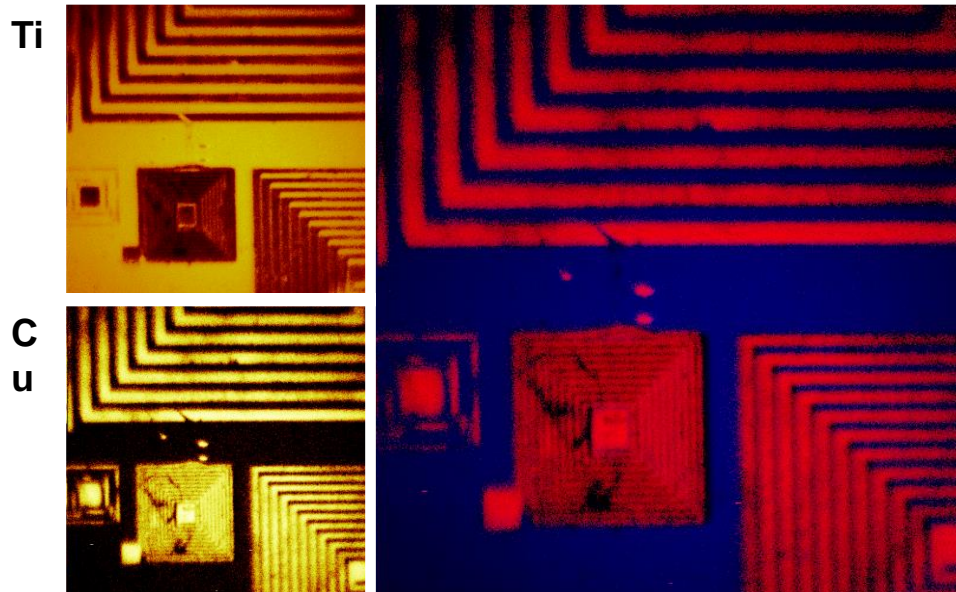


- Imaging
- Surface segregation, anti wetting
- Interdiffusion
- Surface modification
- Nano particles

Lateral Resolution *and* Sensitivity required

Imaging in surface analysis:

- Probe or detector needs sufficient lateral resolution
- Data rate has to be high enough (acquisition time)
- Detection must be sensitive enough
 - sufficient information from each pixel before damage
 - detection sensitivity → “useful lateral resolution”

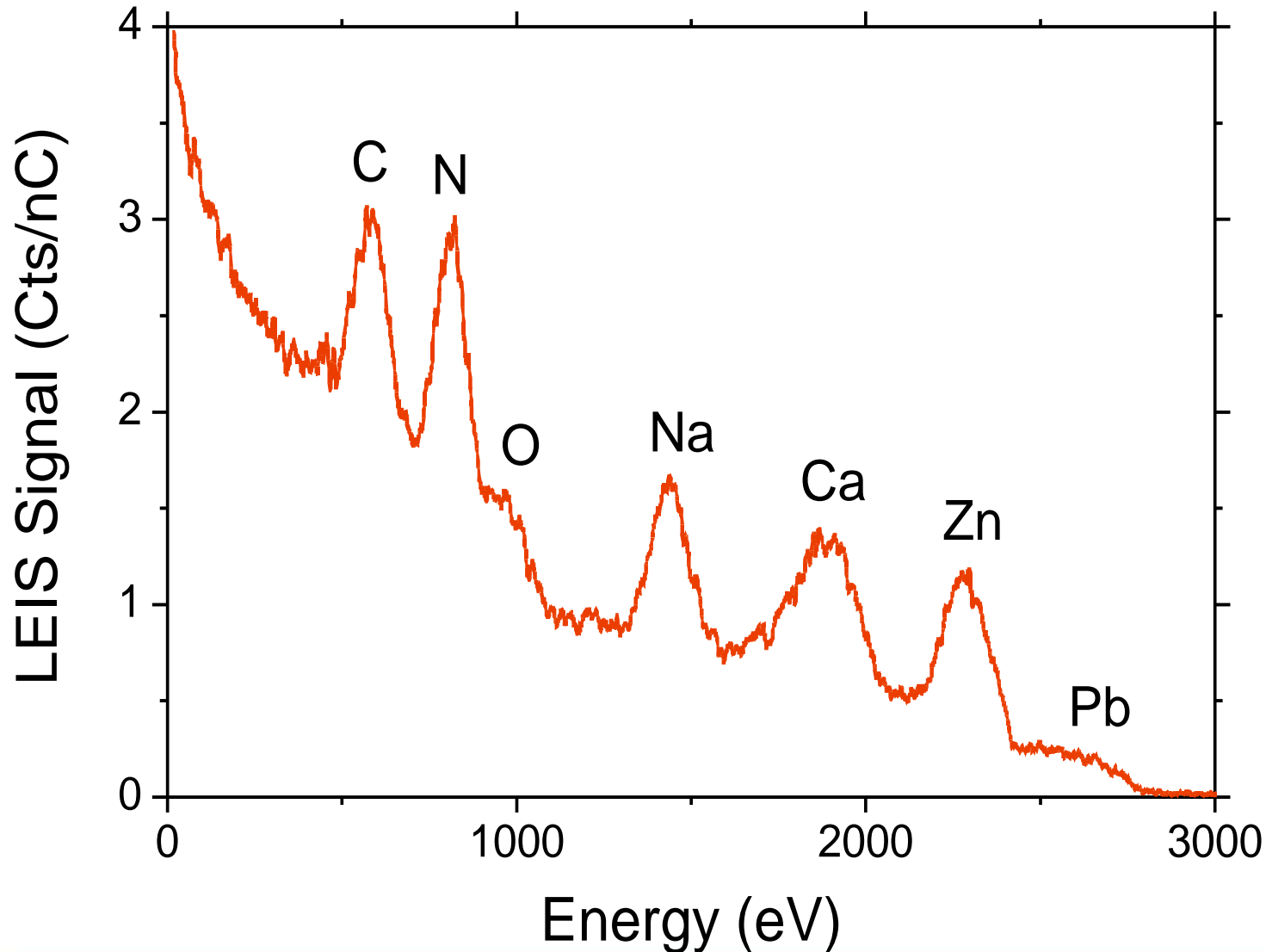


Field of view: 2 mm

With new ion source
lateral resolution
~ 10 μm

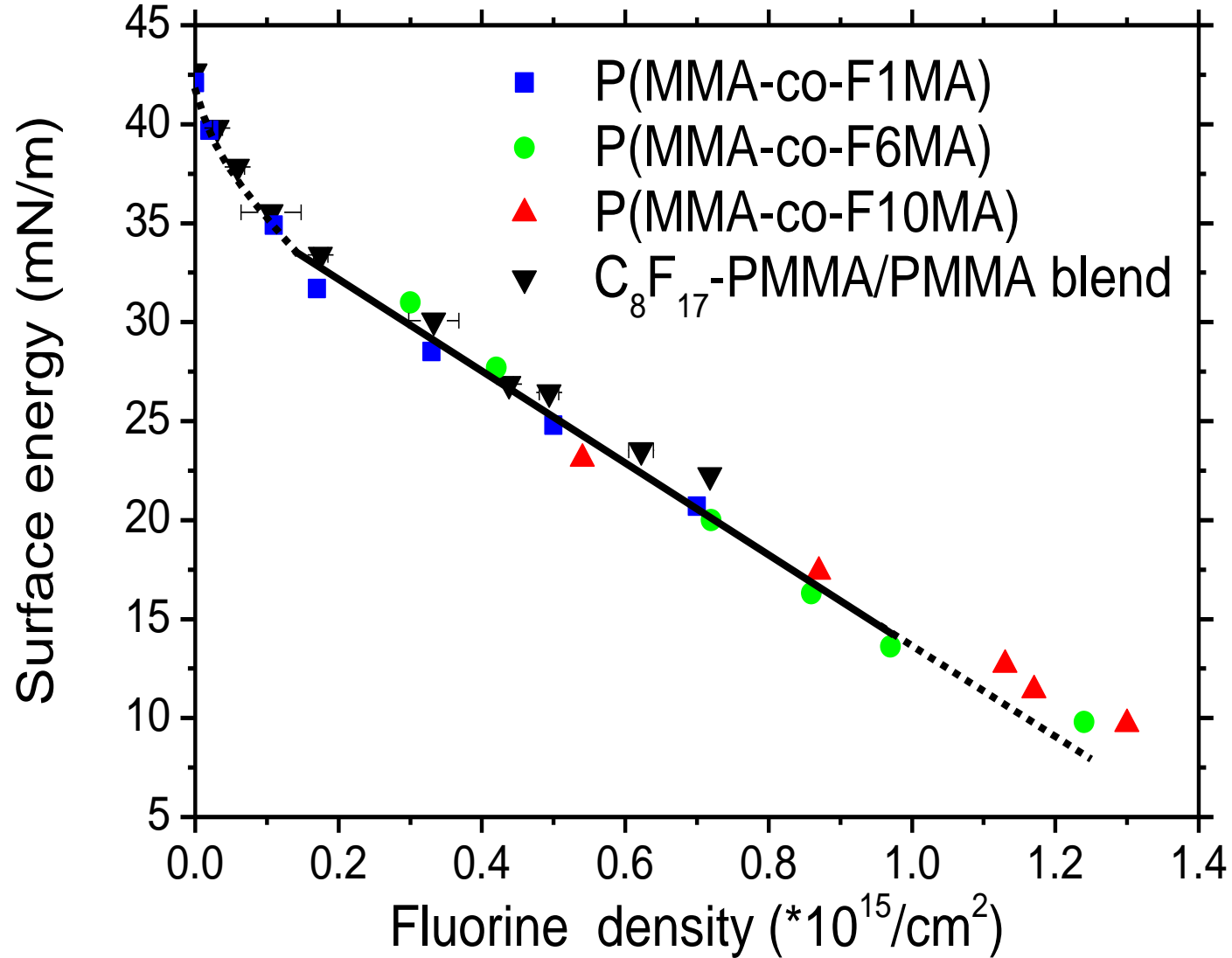
Surface segregation: universal process

Example: Acrylonitrile-Butadiene-Styrene (ABS)

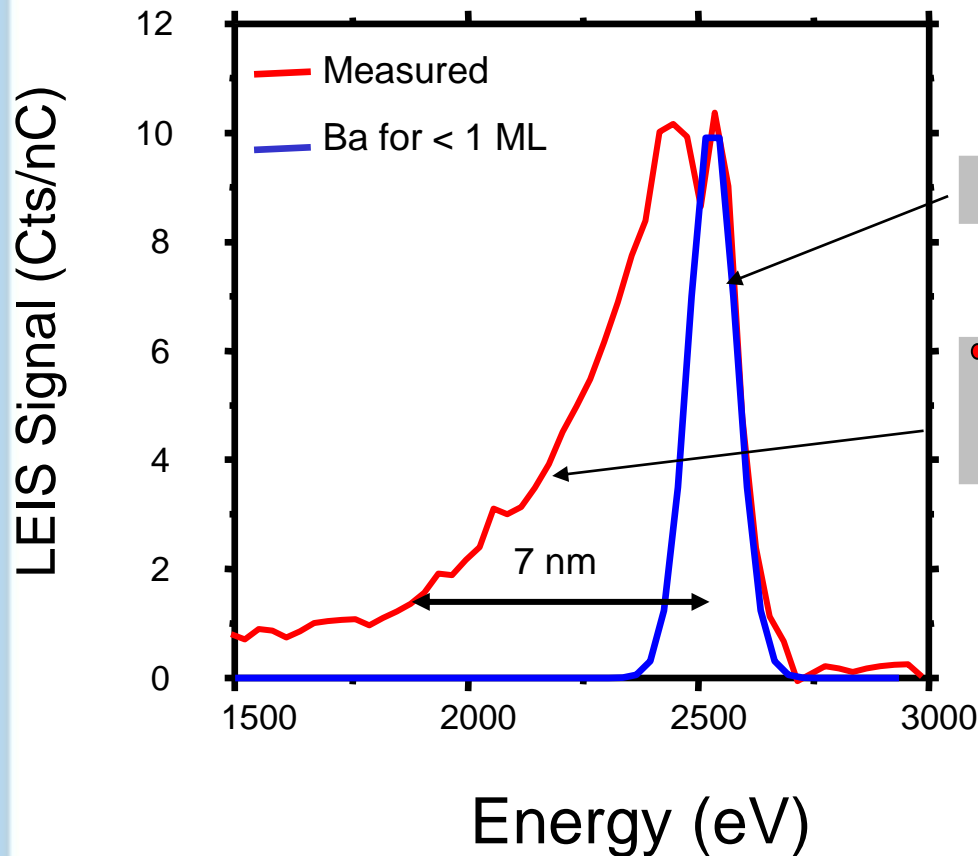


Anti wetting

Fluorine density vs surface energy



PLED: Ba evaporation on PPV



During evaporation of barium on PPV, most of the Ba diffuses into the PPV.

Compare the peakshape of a sub-monolayer of Ba (blue) with the actual peak (red)

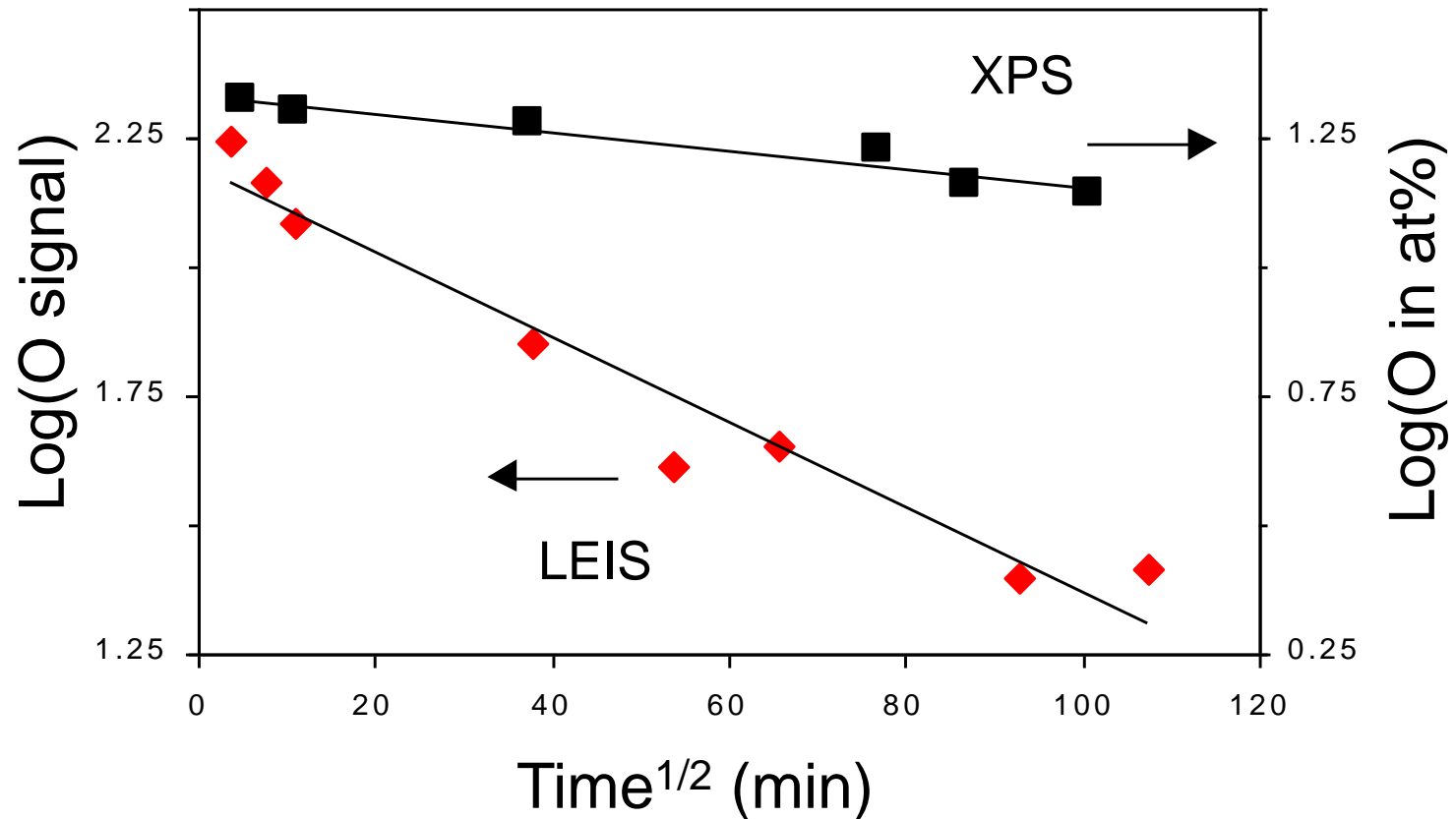
Peak shape \leftrightarrow depth distribution

PLED: higher light output for narrow depth distribution

Surface modification

Aging of plasma oxidized HDPE

- Aging (LEIS) faster than aging (XPS) !
- “Straight line” → diffusion process



Nano particles (supported catalyst)

- Average size
- Core / Shell

Particle Size on Supported Catalysts

Diameter \longleftrightarrow TON; size often related to failure

TEM:



- excellent catalyst characterisation
- detailed info, but local
- contrast required (high Z cluster on low Z support)

Chemisorption:

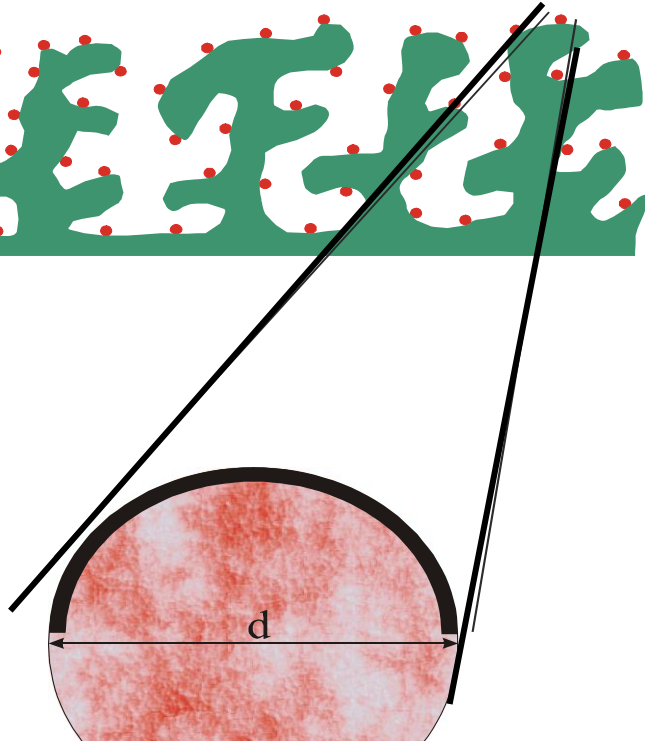
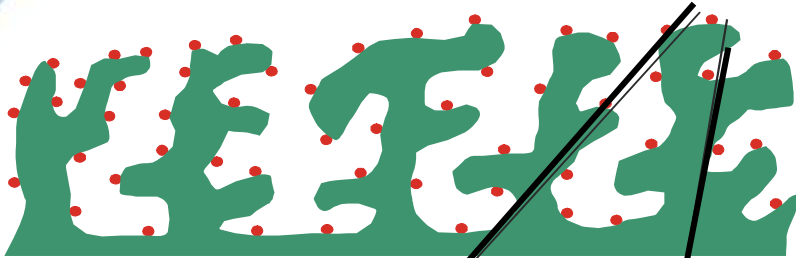
- requires known probe / surface interaction

HS - LEIS:

- new technique; any material; clusters: 1 atom - 10 nm

Comparison:  Richard A. P. Smith (J&M) et al., ECASIA 2009
 T. Tanabe et al. (Toyota), Appl. Catal. A370 (2009) 108

4. Nanoclusters



- Average diameter nanoclusters
- Surface segregation in alloy clusters
- Core/shell particles

(verification, closure, thickness shell)

Example: Three-Way catalyst (exhaust)

Pt clusters on CeO_2 / / γ -alumina

Loading = 0.004 g Pt / γ -alumina

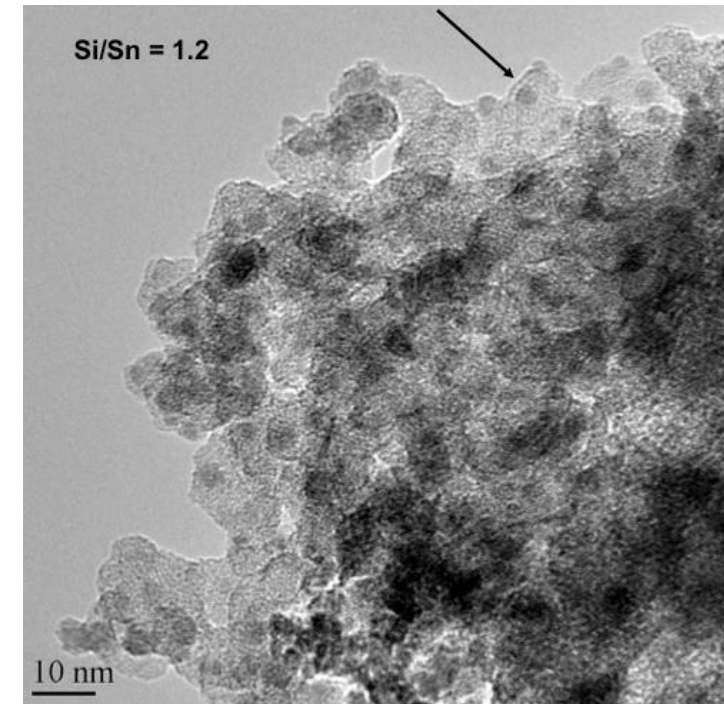
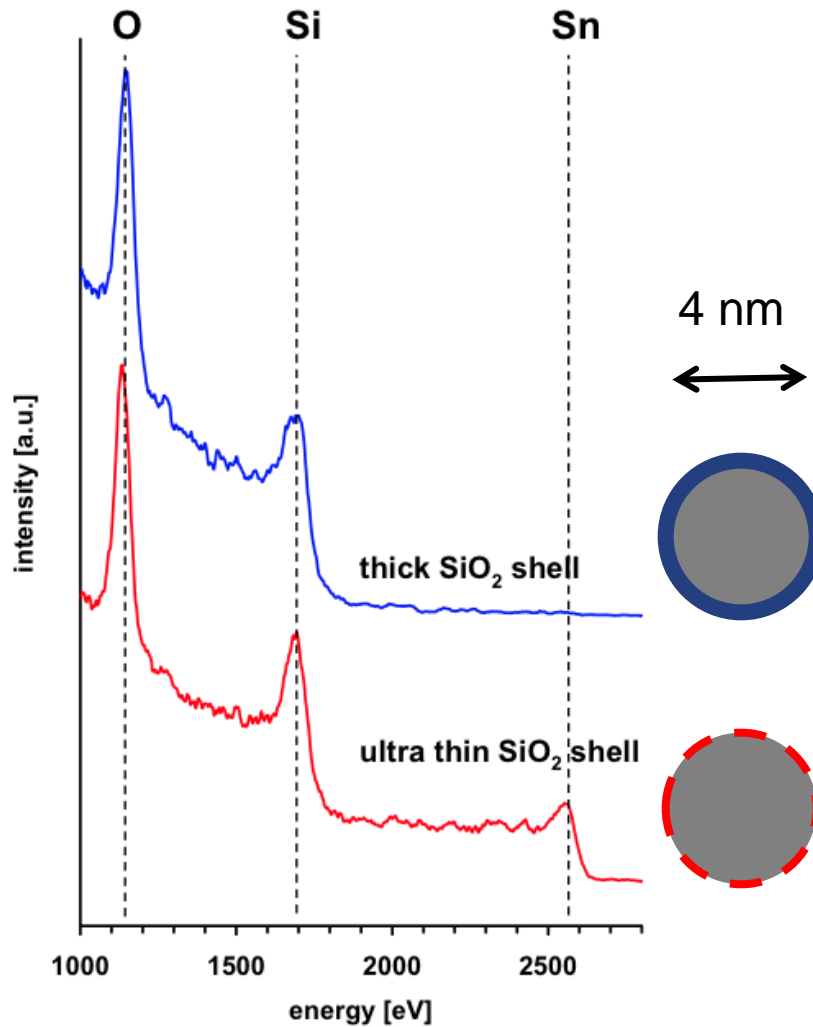
Cluster diameter: 1.6 nm (average)

Accurate for $d < 10$ nm

The diameter is derived from the ratio of the bulk loading (volume) to the LEIS signal (surface area)

This method is possible where TEM fails ($d \leq 2$ nm; high Z support)

Characterisation of Functionalised Core/Shell Nanoparticles

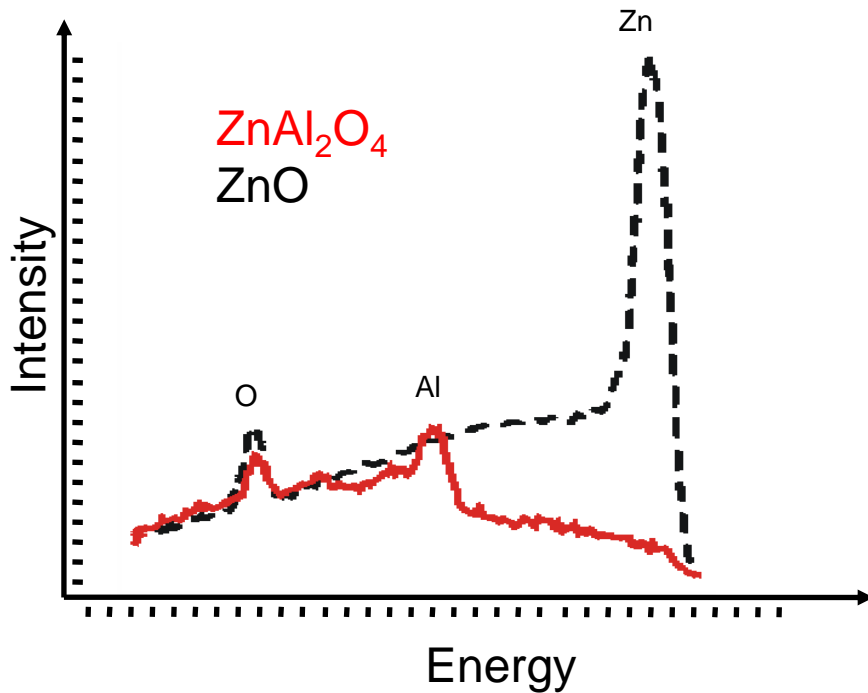


M. Fuchs et al., Surf. Interface Anal. **42** (2010) 1131

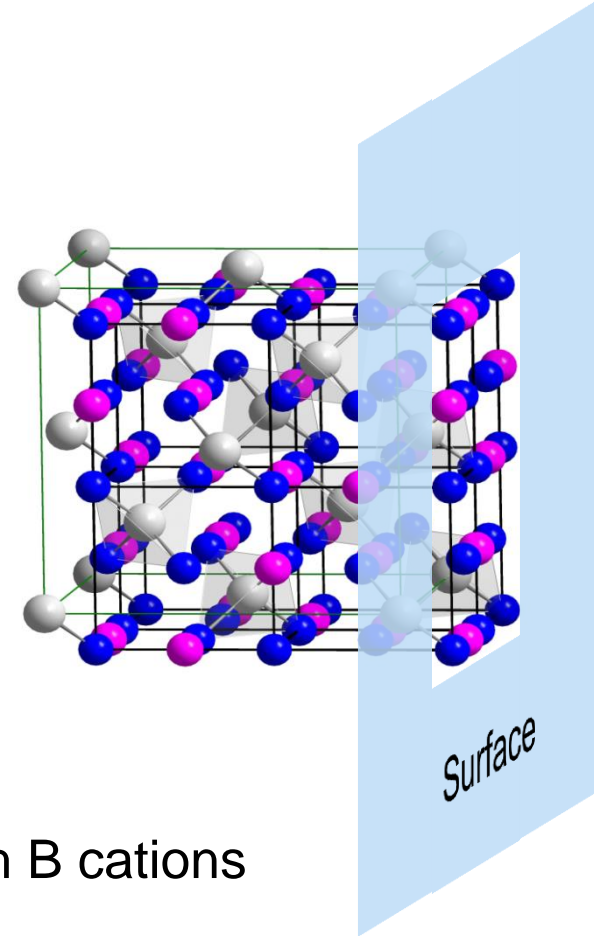
**The outer surface
of
mixed oxides**

LEIS of spinels AB_2O_4

LEIS reveals surface composition powders



- Al
- O
- Zn



Powders: preferential exposure plane with B cations (octahedral sites)

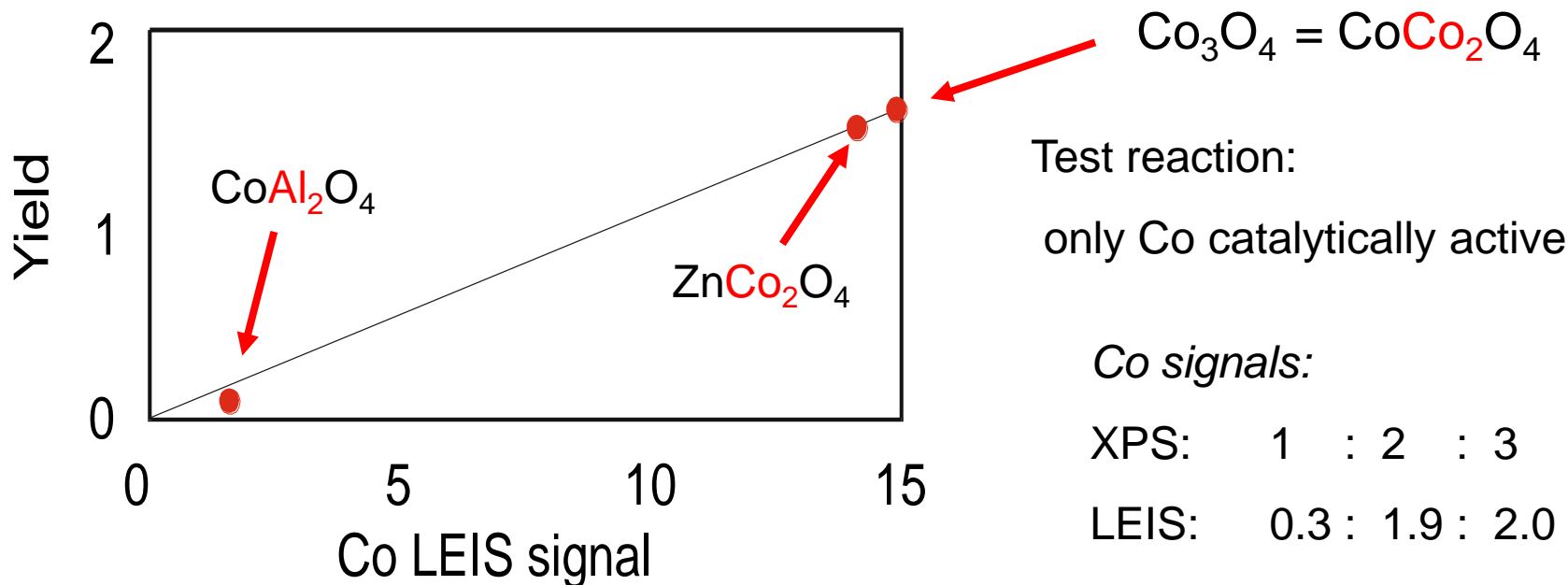
→ Zn in tetrahedral site below surface

Mixed oxides and catalysis

The atomic composition of the 1st atom layer controls catalysis.

In a spinel (AB_2O_4) only the B-cations (octahedral site) are **catalytically active and visible** for LEIS (1st at.).

The A-cations (tetrahedral sites) are in 2nd layer (not active, no LEIS peak).



LEIS



Catalysis

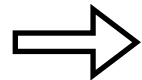



XPS



Spinel (AB_2O_4)

LEIS and chemistry

Cations in octahedral sites at surface (B in normal spinel)

 LEIS
 Chemistry } 1:1 !

Cations in tetrahedral sites below surface (A in normal spinel)

 Chemistry
 LEIS

Perovskites, other oxides: more complicated !
Kilner et al.: LaSrCo oxides

Alumina: difference $\alpha - \gamma$!

Importance of the outer surface

- Performance relies on oxygen transport
- Performance: “ Hampered by the surface ”
- Why ? What is the surface ??

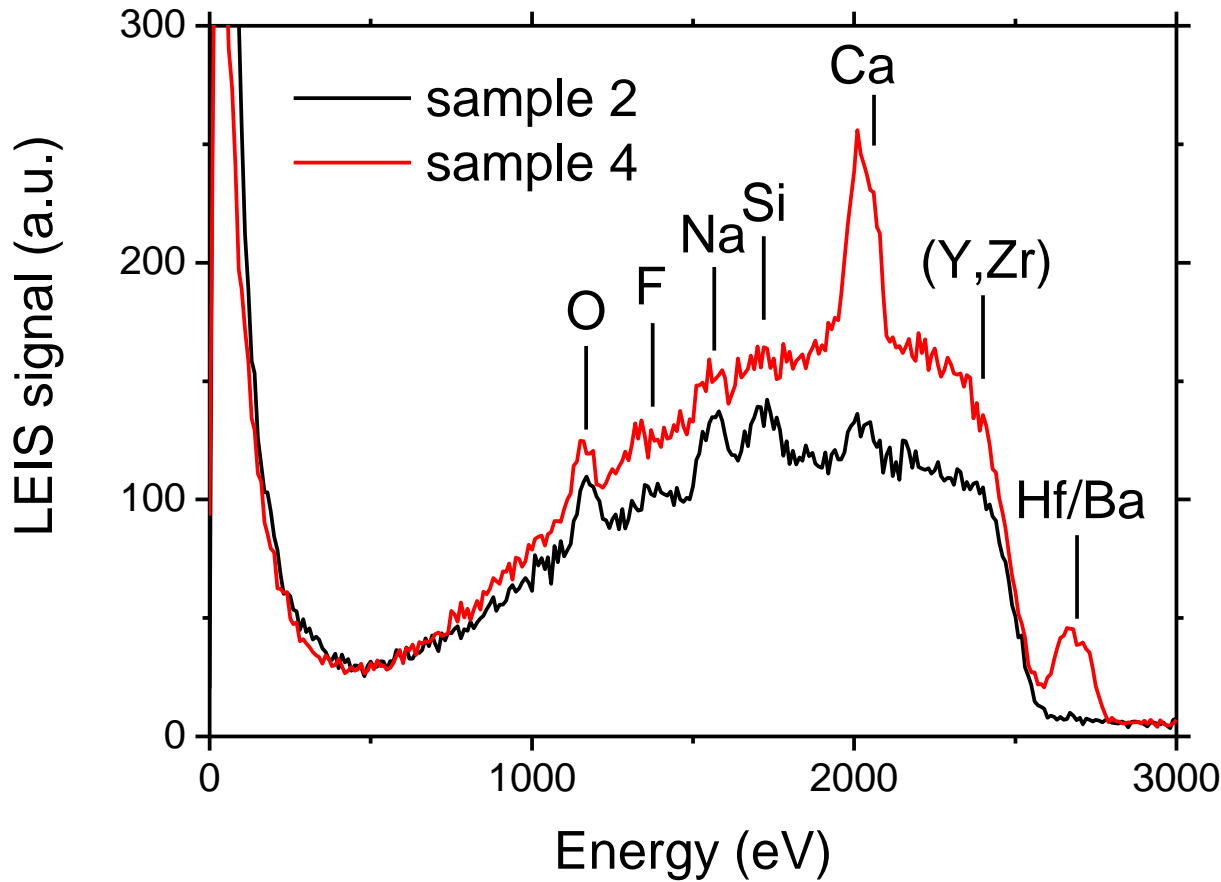
M. de Ridder et al., J. Appl. Phys. 92 (2002) 3056 - 3064

M. de Ridder et al., Solid State Ionics 156 (2003) 255 – 262

J.A. Kilner et al., J. Solid State Electrochem. 15 (2011) 861 - 876

Fuel Cells

Ytria stabilized Zirconia (YSZ) after calcination



Calcination for 5 hours
at 1000 °C in an
oxygen flow of 1.5 bar.



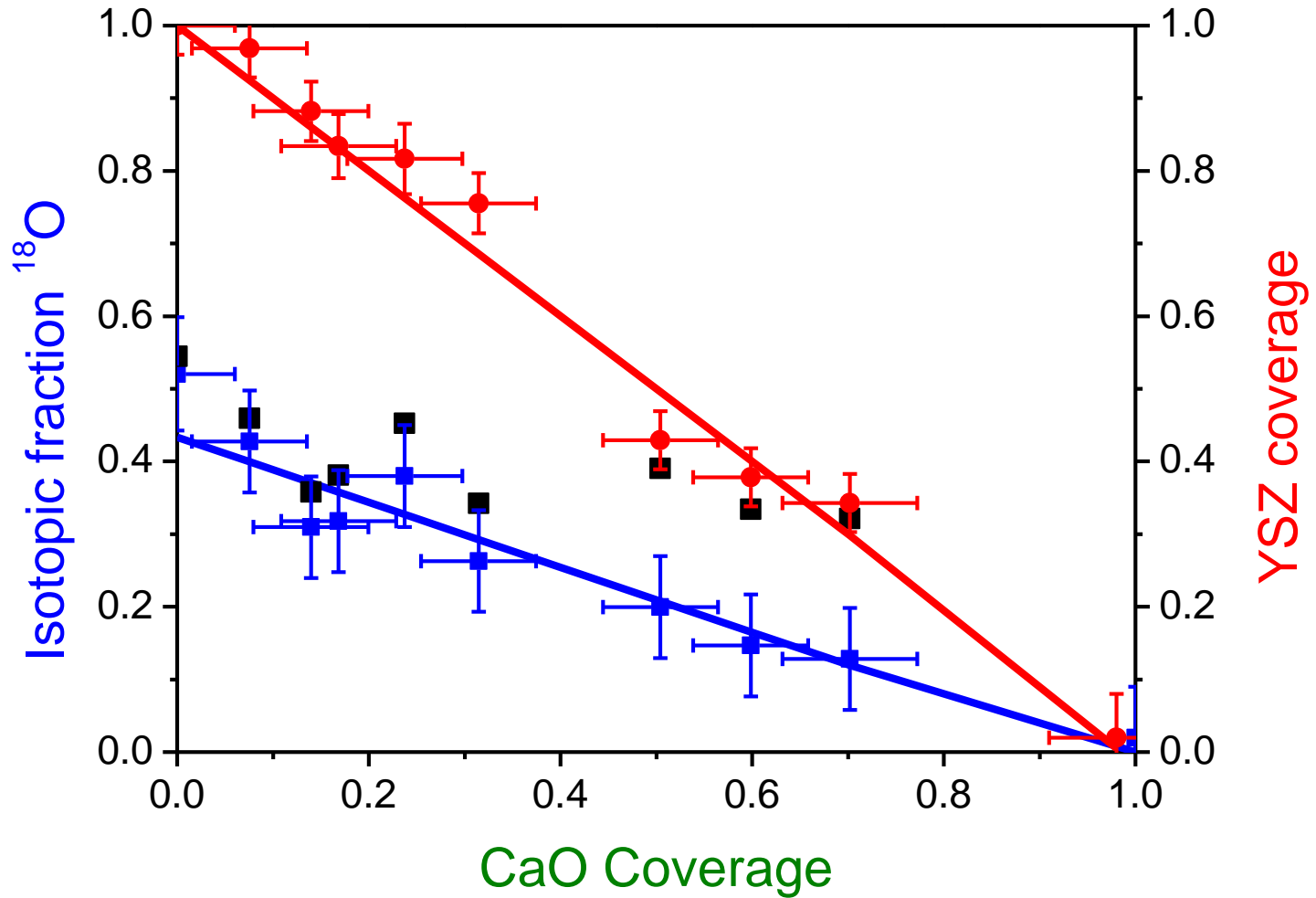
Segregation of
monolayer of
impurities

For $T > 700$ C: No Y, Zr in 1st atom !

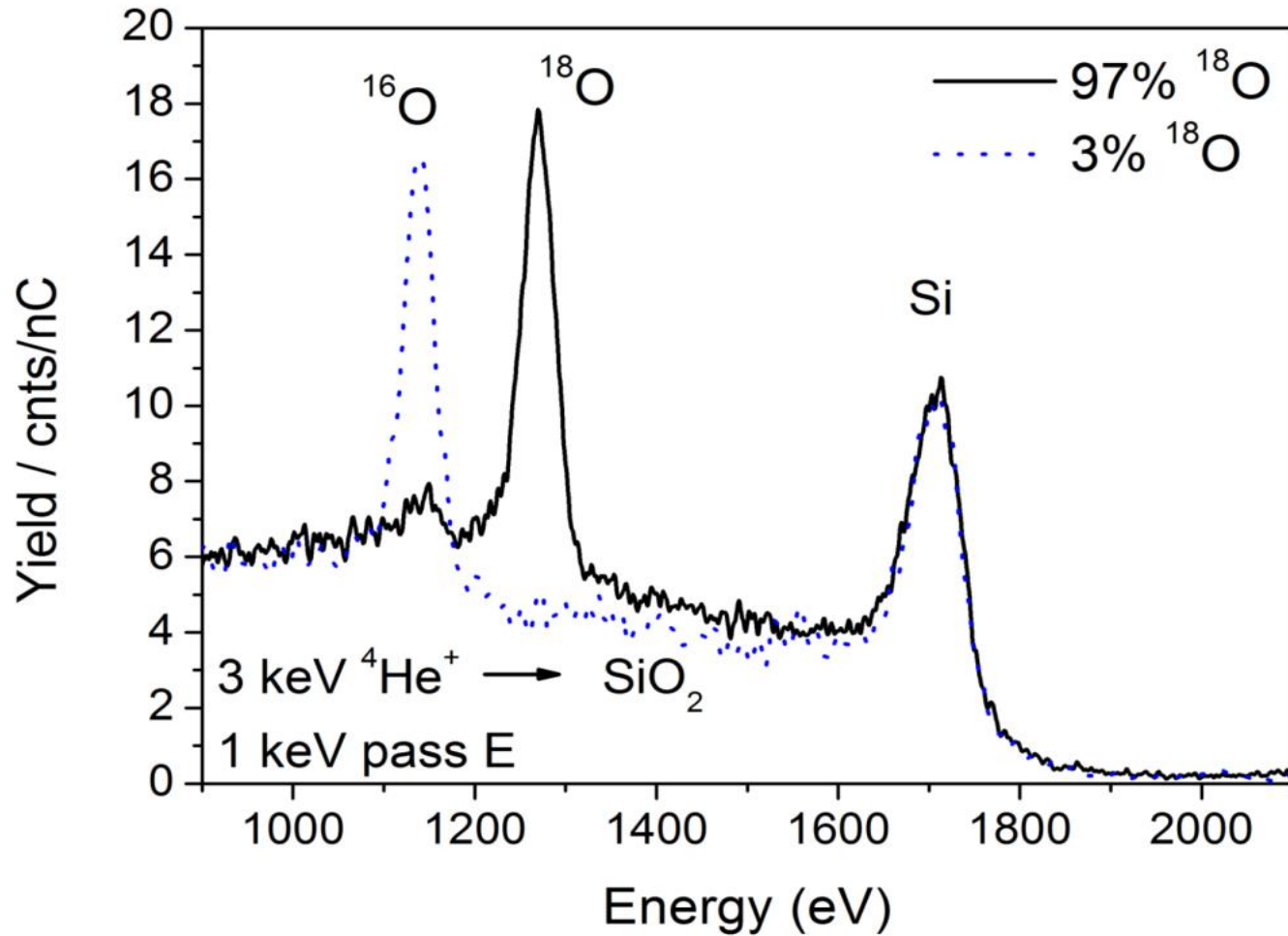
XPS: Ca not visible (\leftrightarrow Zr)

Fuel Cells

CaO coverage blocks $^{16}\text{O} - ^{18}\text{O}$ exchange



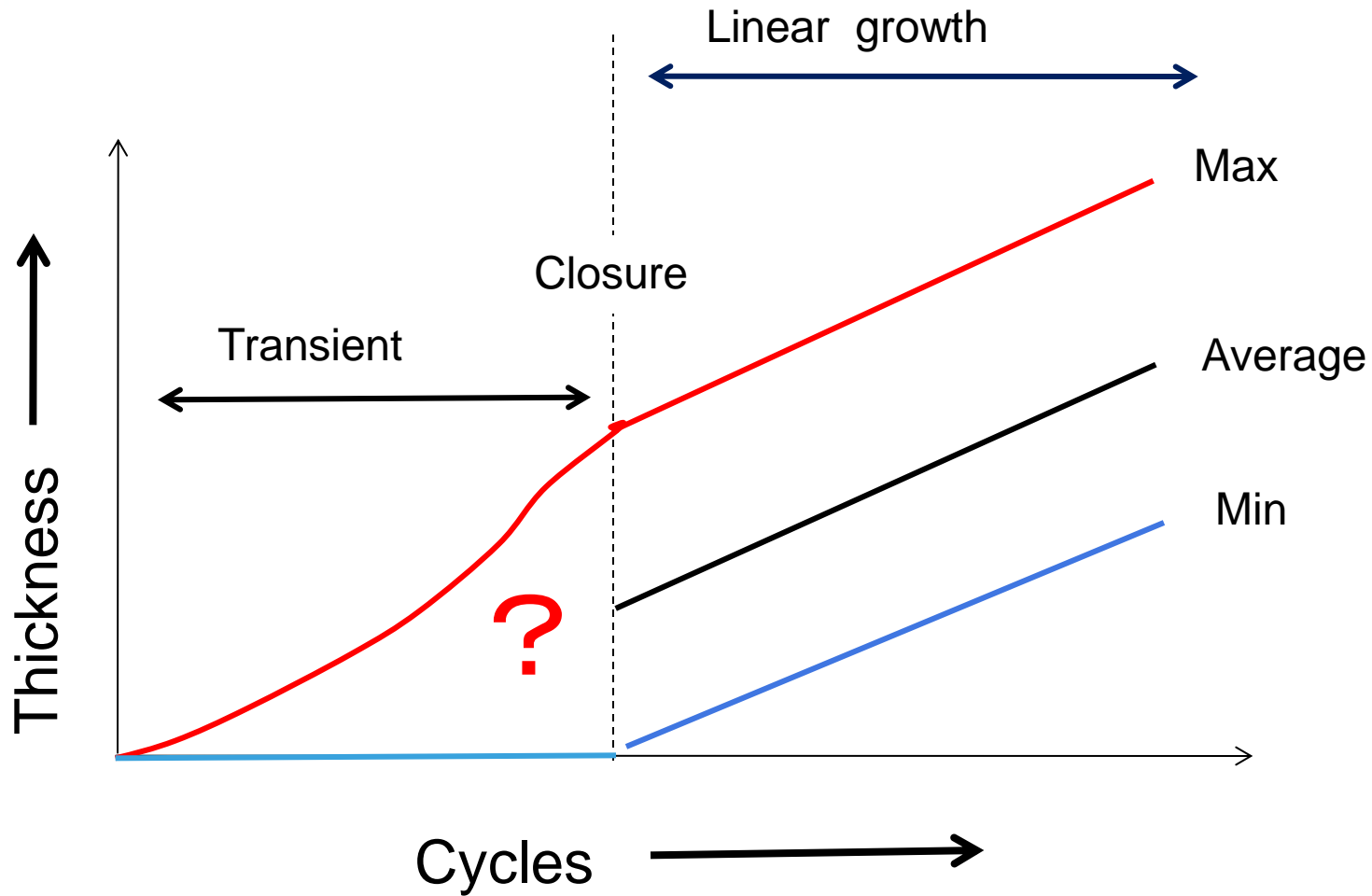
Isotopic exchange 16O – 18O



H. Téllez, R. J. Chater, S. Fearn, E. Symianakis, H. H. Brongersma, J.A. Kilner
Appl. Phys. Lett. 101, 151602 (2012)

Growth of Ultra thin

Layer thickness versus cycle



The transient regime determines the uniformity of the layer

Transient regime (growth before closure) (6 up to > 150 cycles !)

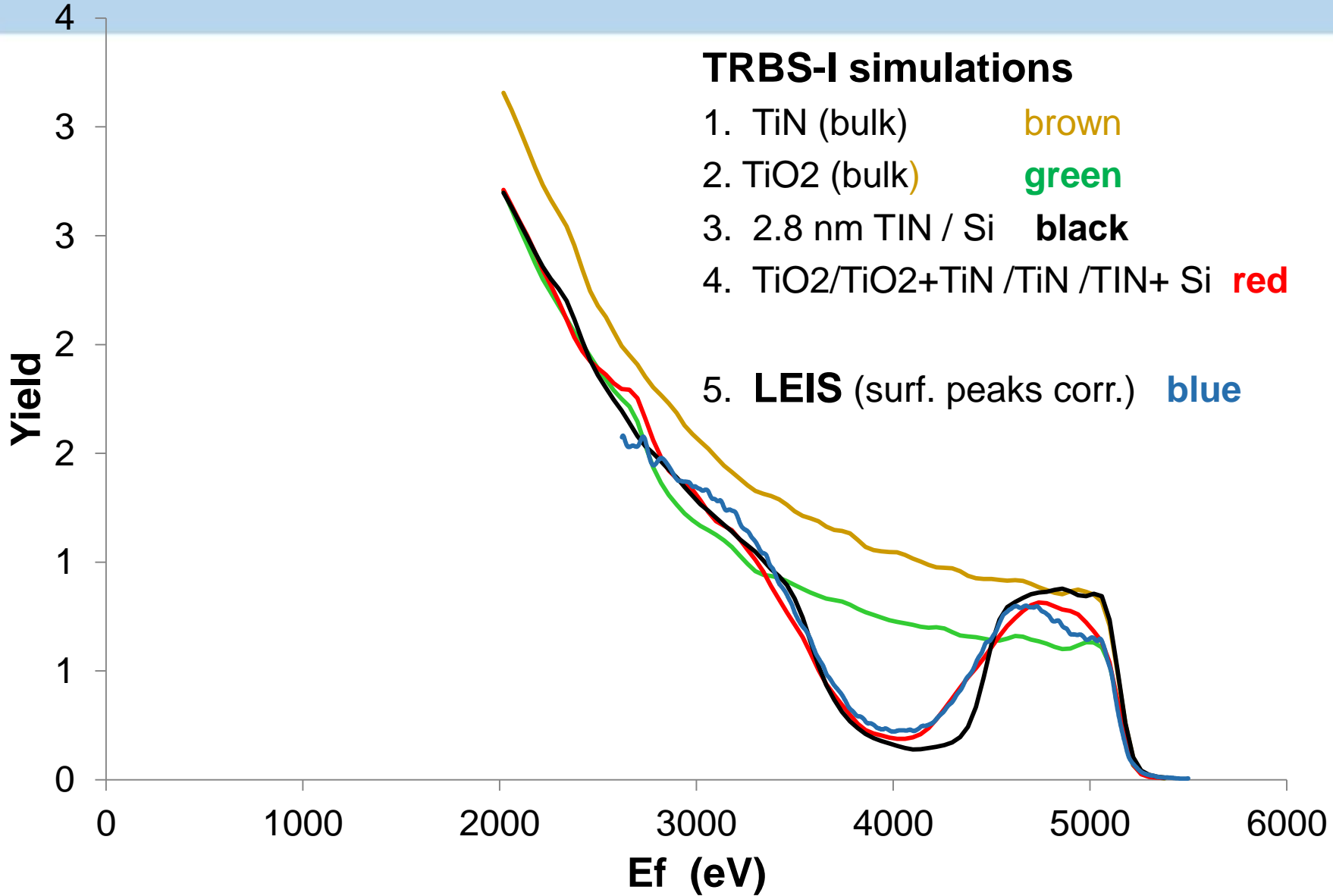
Width of the transient regime depends on nucleation of ALD reaction, precursors and growth mode

- **2D growth:** Preferential growth on substrate
CrOx/Al₂O₃, ZrO₂/SiO₂, HfO₂/Si
- **Random growth** AlN/Al₂O₃, AlN/SiO₂, Fe₂O₃/ZrO₂
- **3D growth:** Preferential growth on pre-deposited matter
Ni/Al₂O₃, HfO₂/Ge, WNC/SiO₂/Si, Ta(CN)/SiO₂/Si, Ta(Si)/SiO₂/Si, TiN/SiO₂,
Al₂O₃/Si-H, ZrO₂/Si-H

Controlling the transient regime is fundamental for continuity of ultrathin ALD films. **ALD + LEIS !!**

7 keV He+ LEIS

3.0 nm TiN / Si(100) nominal



Growth of Ultra-thin layers

LEIS: *1st atom + in-depth, quantitative, sensitive*

- Initial growth
 - Poisoning, activation
 - Pinholes
 - Diffusion
 - Thickness uniformity
- Use LEIS in the optimization of growth processes (ALD!)

Summary

- Sensitivity
- 1st atom + in-depth
- Surf. segr. / anti wetting / M – polymer / surf. Modific. / NPs / graphene
- Outer surface of oxides
- SOFC , membranes
- ALD growth

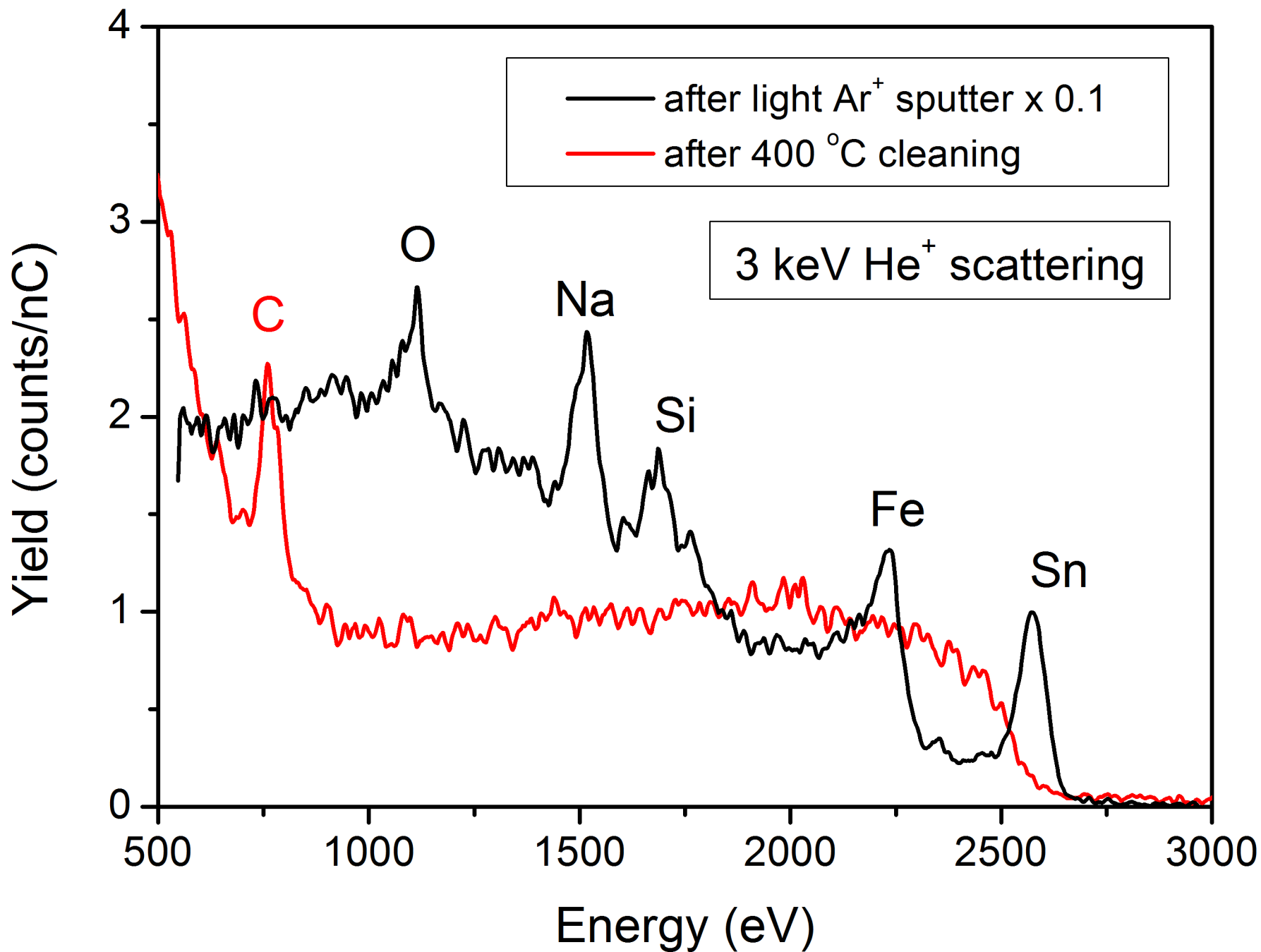
Miscellaneous applications

- Catalysts, microelectronics, polymers, (bio-) sensors,

But also:

- Candy wrappers
- F 16 dome, windows of planes
- Bone tissue, dental implants, stents,
- Aging of linoleum (“ Linowonder”)
- Anti-wetting (watches, diapers,
- Floor wax





Graphene analysis with LEIS ??

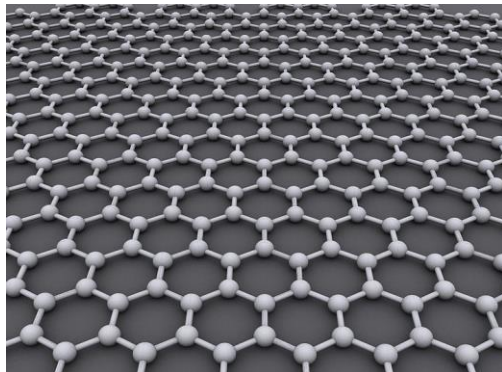
Wishes:

- Determination layer thickness, layer integrity
- Distinguish and Quantify carbon allotropes
- Detection contaminants / dopants *on/in* and *below* the film (intercalation)

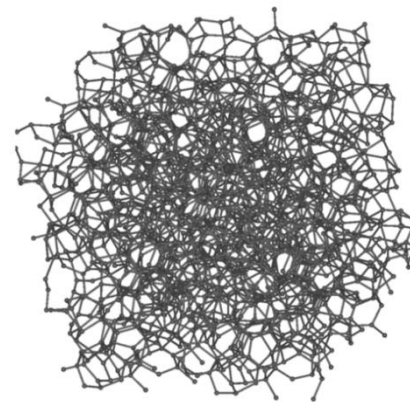
LEIS ??

- Carbon: low Z ➡ Low sensitivity
- Monolayer depth info? Carbon atoms very small
- Distinguish allotropes ? No matrix effects (in general)

LEIS seems useless for studying graphene, but :



Author: AlexanderAIUS, wikipedia

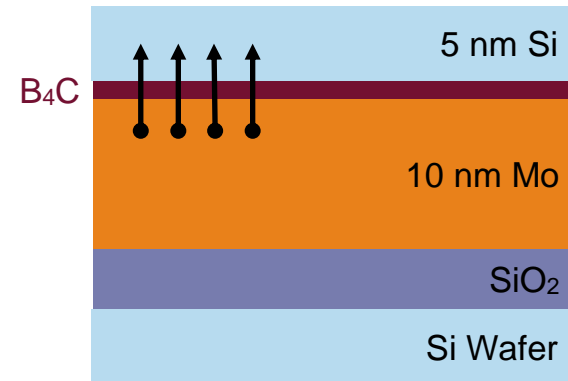
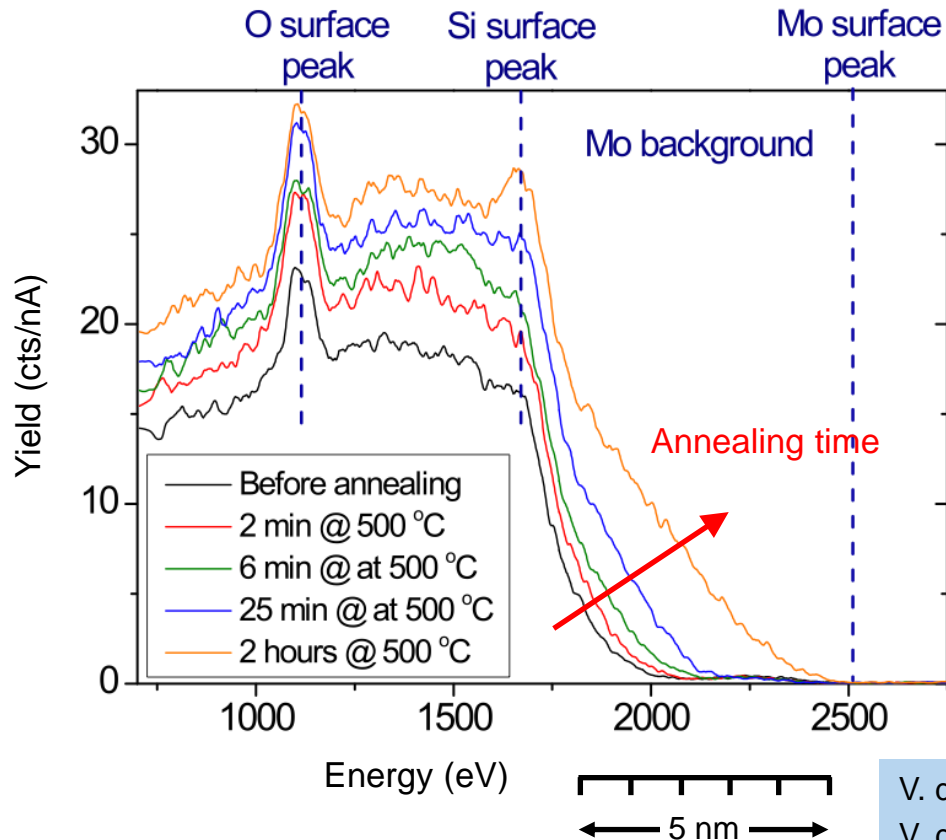


Author: Mstroeck, wikipedia

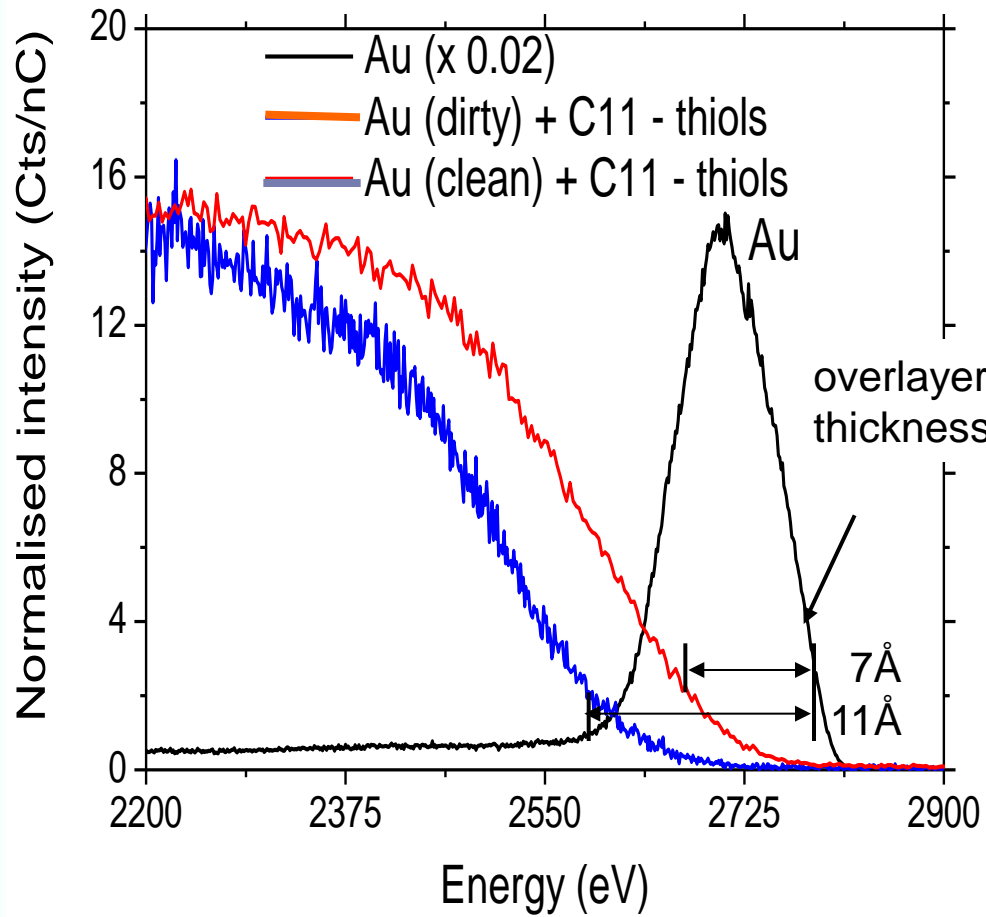
Diffusion study with in-situ heating

Mo/Si layer – quantification of diffusion constant

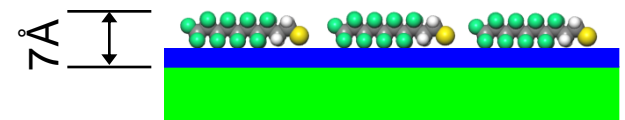
- 5 nm Si / 1.6 nm B₄C / 10 nm Mo, annealing @ 500 deg. C
- Diffusion coefficient without B₄C : $(8 \pm 2) \cdot 10^{-20}$ m²/s
- Diffusion coefficient with 1.6 nm B₄C: $(4 \pm 1) \cdot 10^{-21}$ m²/s



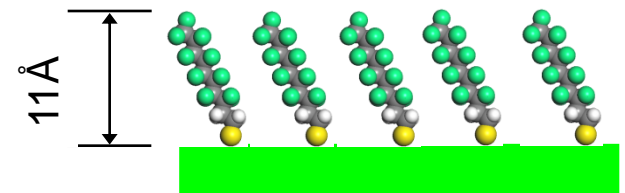
High-energy edge of SAMs on Au

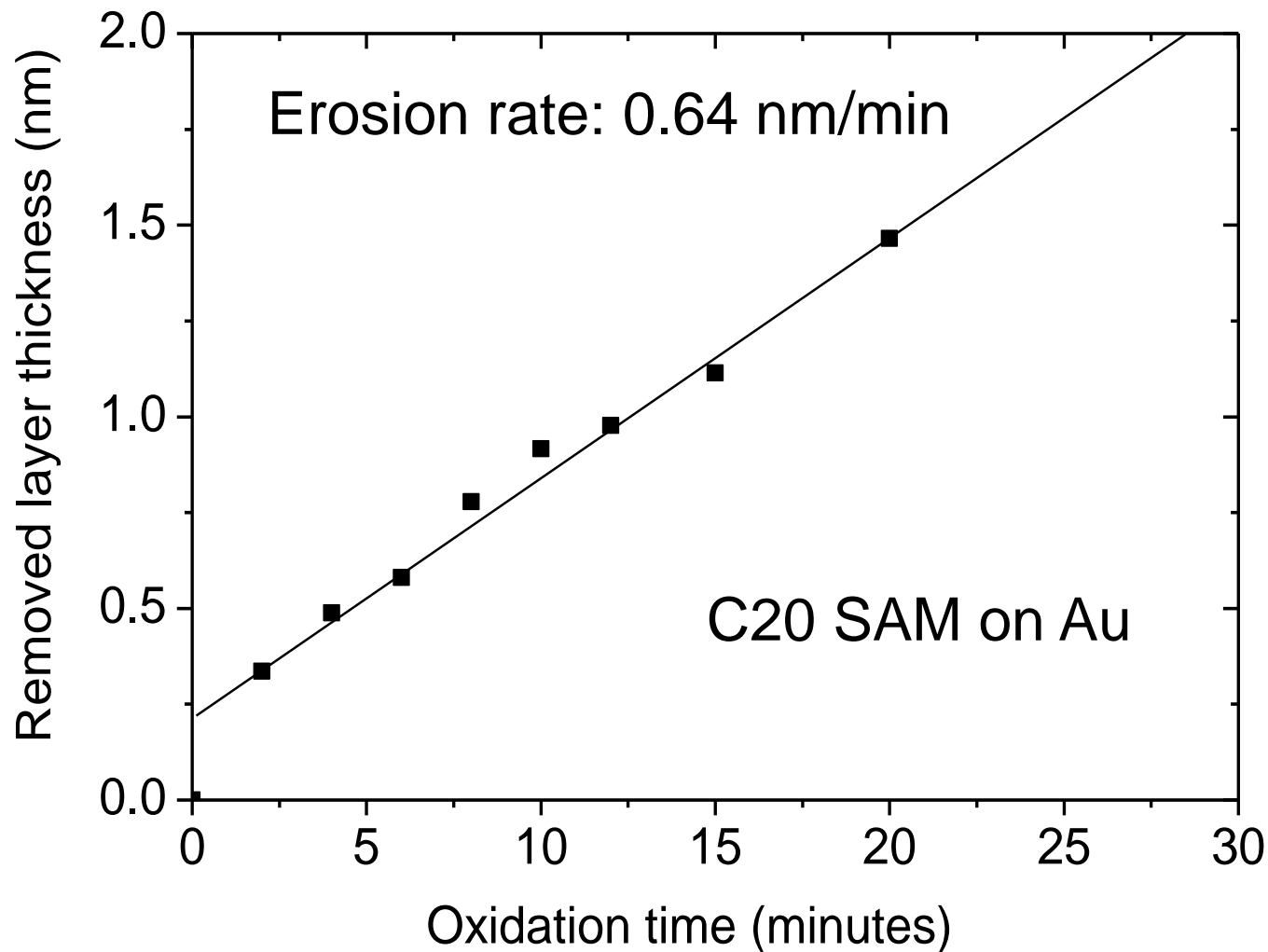


Fluorinated thiol on **dirty** Au surface

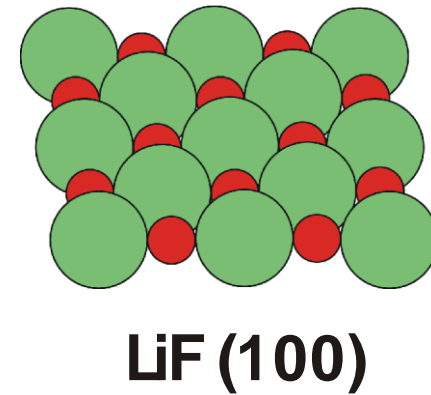
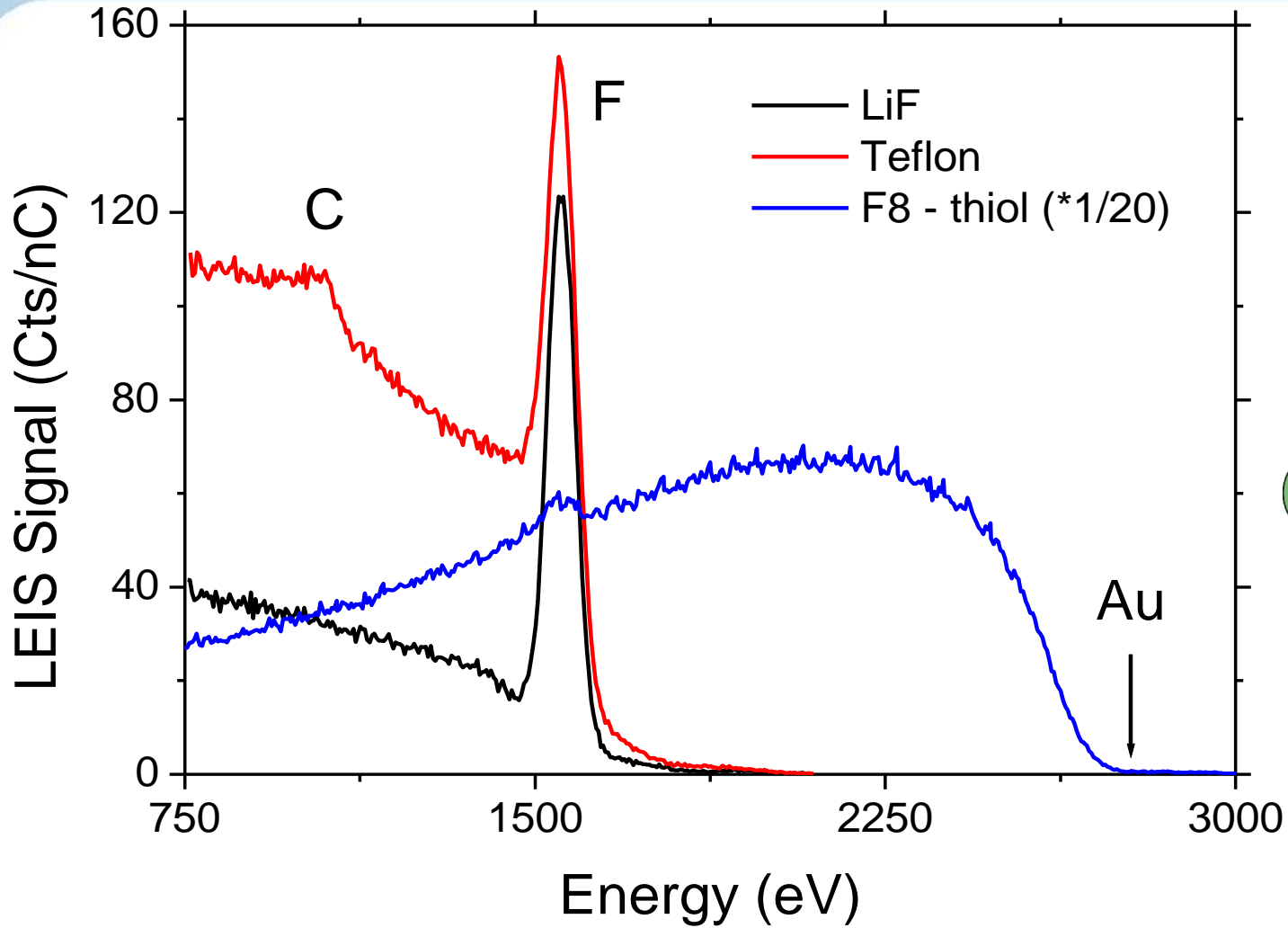


Fluorinated thiol on **clean** Au surface





Quantification of F with LiF(100)



LiF(100) : Teflon : s.-a. ML = 1.23 : 1.24 : $1.48 \cdot 10^{15}$ at./cm²

Outer and Near surface of Perovskites

by LEIS (for Fuel Cells and Oxygen Membranes)

Outer surface: **A-site** termination (LEIS: no other cations)

Subsurface: Layered oxide (LEIS depth profiling)

Examples:

Structure



Perovskite



Double Perovskite



Ruddlesden - Popper